

**TMN2006MI**

**N-Channel Enhancement Mosfet**

**General Description**

- Low  $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

**Applications**

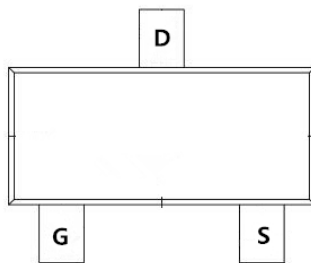
- Load switch
- PWM

**General Features**

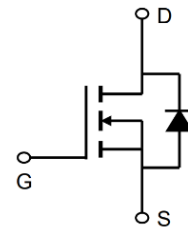
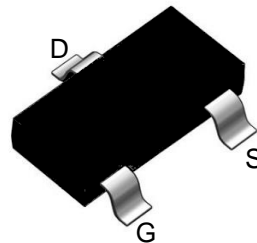
$V_{DS} = 20V$   $I_D = 6.2A$

$R_{DS(ON)} = 19m\Omega$  (Typ.) @  $V_{GS} = 4.5V$

100% UIS Tested  
 100%  $R_g$  Tested



MI:SOT-23-3L



Marking: 2300

**Absolute Maximum Ratings ( $T_c = 25^\circ C$  unless otherwise noted)**

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	6.2	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V^1$	3.0	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	16.4	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation <sup>3</sup>	1.0	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ C$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ C$

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	---	170	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	---	$^\circ C/W$

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**Electrical Characteristics** ( $T_J=25^\circ\text{C}$  unless otherwise specified)

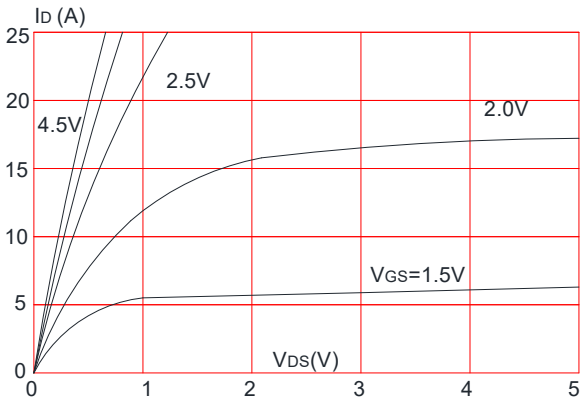
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=20V, V_{GS}=0V,$	-	-	1.0	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4	0.7	1	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note2</small>	$V_{GS}=4.5V, I_D=4A$	-	18	24	m $\Omega$
		$V_{GS}=2.5V, I_D=3A$	-	25	41	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS}=10V, V_{GS}=0V,$ $f=1.0MHz$	-	358	-	pF
$C_{oss}$	Output Capacitance		-	69.3	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	58.5	-	pF
$Q_g$	Total Gate Charge	$V_{DS}=10V, I_D=2A,$ $V_{GS}=4.5V$	-	5.6	-	nC
$Q_{gs}$	Gate-Source Charge		-	0.8	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	1	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DS}=10V,$ $I_D=4A, R_{GEN}=3\Omega,$ $V_{GS}=4.5V$	-	5	-	ns
$t_r$	Turn-on Rise Time		-	30	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	48	-	ns
$t_f$	Turn-off Fall Time		-	36	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	6	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	16	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=4A$	-	-	1.2	V

Notes: 1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

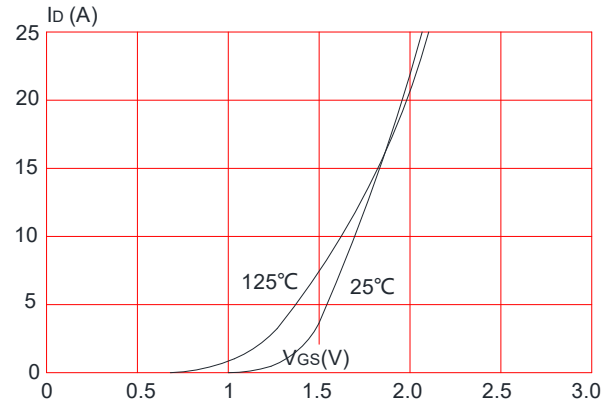
 2. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 0.5\%$

**Typical Performance Characteristics**

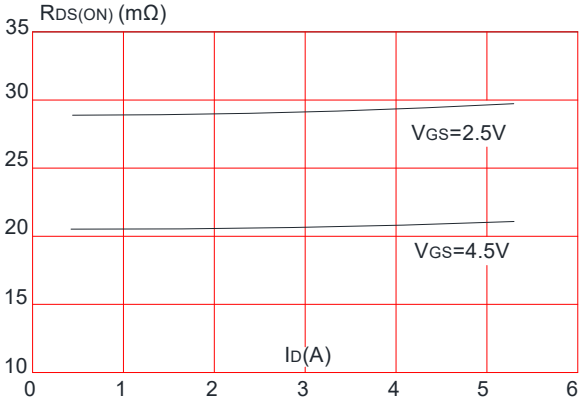
**Figure 1: Output Characteristics**



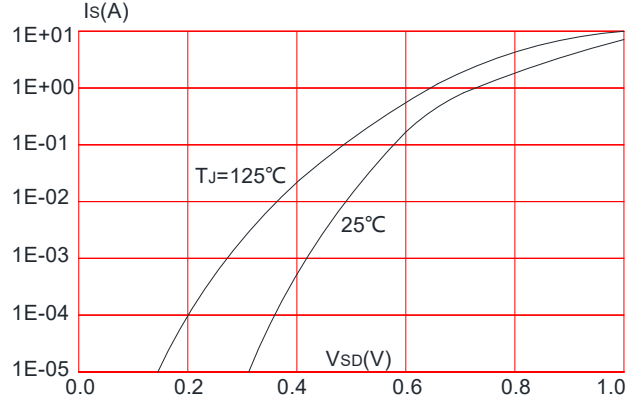
**Figure 2: Typical Transfer Characteristics**



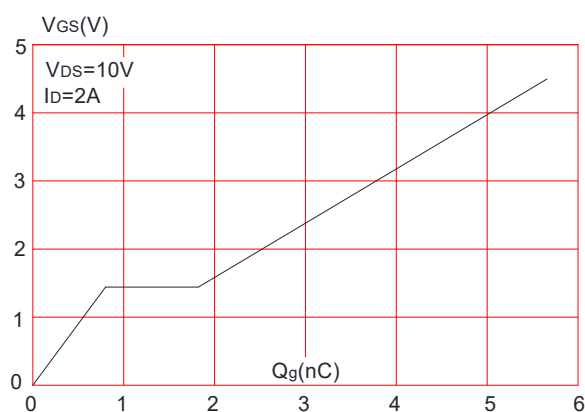
**Figure 3: On-resistance vs. Drain Current**



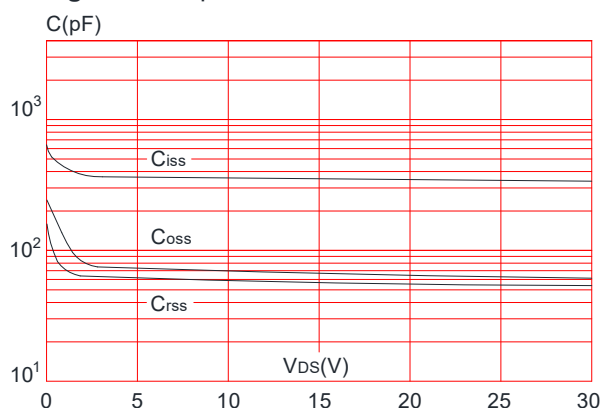
**Figure 4: Body Diode Characteristics**



**Figure 5: Gate Charge Characteristics**



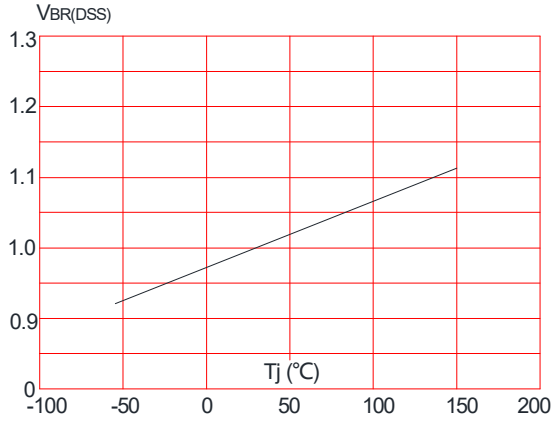
**Figure 6: Capacitance Characteristics**



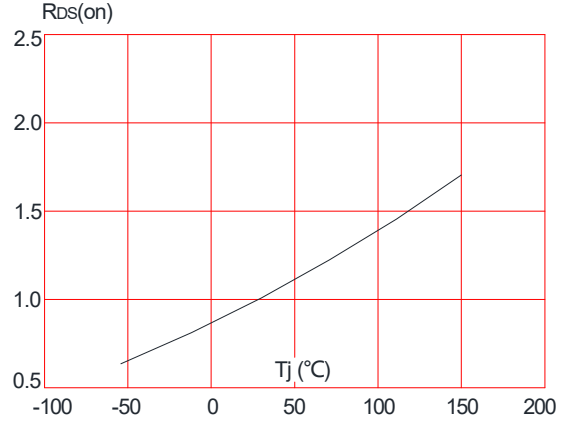
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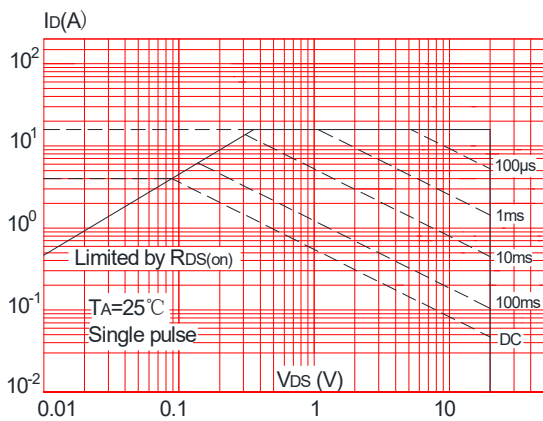
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



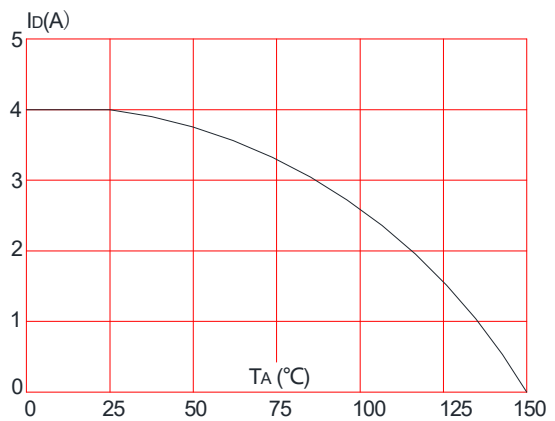
**Figure 8:** Normalized on Resistance vs. Junction Temperature



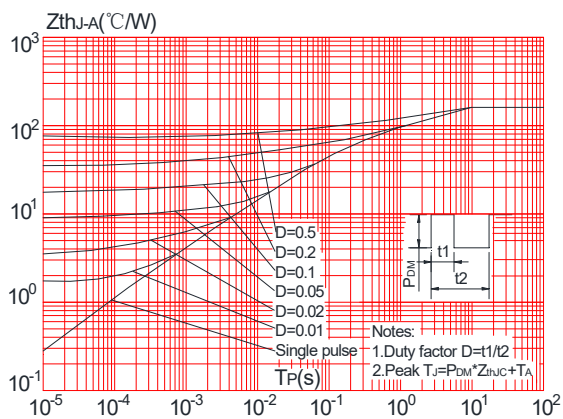
**Figure 9:** Maximum Safe Operating Area



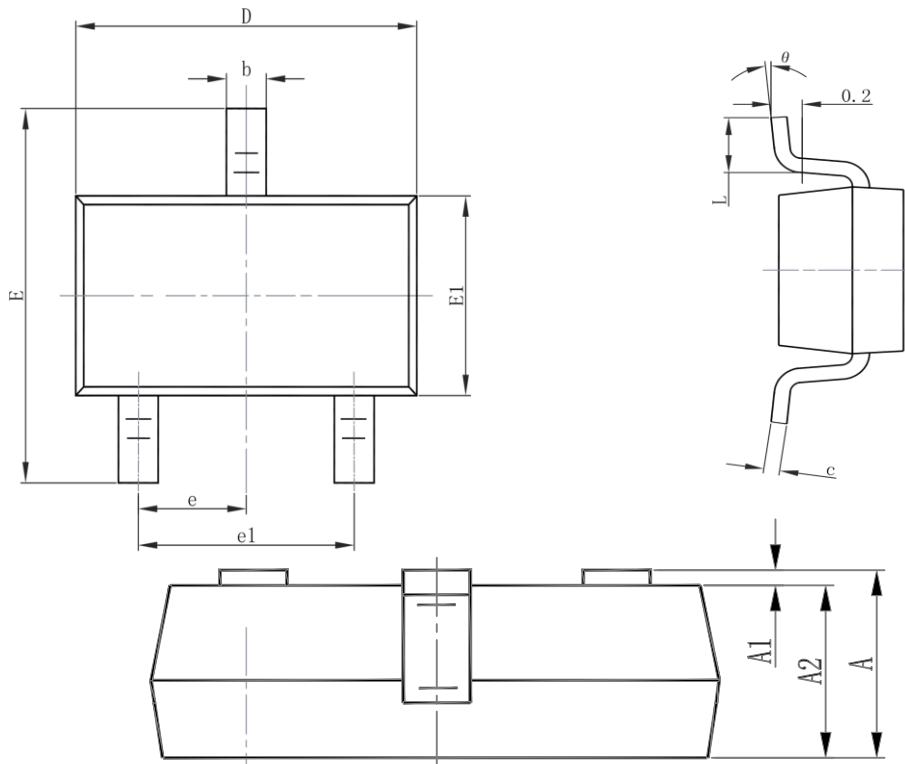
**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



## Package Information:SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°

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